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November 2013

FQD2N80

N-Channel QFET® MOSFET

800 V, 1.8 A, 6.3 Ω

Description

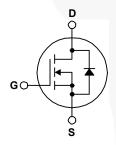
This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance • Low Crss (Typ. 5.5 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

Features

- 1.8 A, 800 V, $R_{DS(on)} = 6.3 \Omega$ (Max.) @ $V_{GS} = 10 V$, $I_D = 0.9 A$
- Low Gate Charge (Typ. 12 nC)

- · RoHS Compliant





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQD2N80TM	Unit	
V _{DSS}	Drain-Source Voltage		800	V	
I _D	Drain Current - Continuous (T _C = 25°C)		1.8	А	
	- Continuous (T _C = 100°C)		1.14	А	
I _{DM}	Drain Current - Pulsed	(Note 1)	7.2	А	
V _{GSS}	Gate-Source Voltage		± 30	V	
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	180	mJ	
I _{AR}	Avalanche Current	(Note 1)	1.8	Α	
E _{AR}	Repetitive Avalanche Energy	(Note 1)	5.0	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.0	V/ns	
P _D	Power Dissipation (T _A = 25°C) *		2.5	W	
	Power Dissipation (T _C = 25°C) - Derate above 25°C		50	W	
			0.4	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C	
TL	Maximum lead temperature for soldering, 1/8" from case for 5 seconds		300	°C	

Thermal Characteristics

Symbol	Parameter	FQD2N80TM	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.		
В	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	50	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQD2N80TM	FQD2N80	DPAK	Tape and Reel	330 mm	16 mm	2500 units

Electrical Characteristics

T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	800			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		0.9		V/°C
I _{DSS}	7 0 1 1/1 1 2 1 0 1	V _{DS} = 800 V, V _{GS} = 0 V			10	μΑ
	Zero Gate Voltage Drain Current	V _{DS} = 640 V, T _C = 125°C			100	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 0.9 A		4.9	6.3	Ω
9 _{FS}	Forward Transconductance $V_{DS} = 50 \text{ V}, I_{D} = 0.9 \text{ A}$			2.4		S
•	ic Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		425	550	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		45	60	pF
C _{rss}	Reverse Transfer Capacitance			5.5	7.0	pF
Switchi	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	V = 400 V L = 2.4.A		12	35	ns
t _r	Turn-On Rise Time	$V_{DD} = 400 \text{ V}, I_D = 2.4 \text{ A},$ $R_G = 25 \Omega$		30	70	ns
t _{d(off)}	Turn-Off Delay Time	NG - 20 32		25	60	ns
t _f	Turn-Off Fall Time	(Note 4)		28	65	ns
Q _g	Total Gate Charge	V _{DS} = 640 V, I _D = 2.4 A,		12	15	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = 10 \text{ V}$		2.6		nC
Q _{gd}	Gate-Drain Charge	(Note 4)	/	6.0		nC
Drain S	Source Diede Characteristics a	nd Maximum Patings				
I _S	Source Diode Characteristics and Maximum Ratings Maximum Continuous Drain-Source Diode Forward Current				1.8	Α
I _{SM}	Maximum Pulsed Drain-Source Diode F	Forward Current			7.2	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 1.8 A			1.4	V
t _{rr}	Reverse Recovery Time $V_{GS} = 0 \text{ V, I}_{S} = 2.4 \text{ A},$			480		ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs		2.0	//	μС

- ${\bf 1.}\ {\bf Repetitive}\ {\bf rating: pulse-width\ limited\ by\ maximum\ junction\ temperature.}$
- 2. L = 105 mH, I_{AS} = 1.8 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C. 3. I_{SD} \leq 2.4 A, di/dt \leq 200 A/µs, V_{DD} \leq BV_{DSS}, starting T_J = 25°C. 4. Essentially independent of operating temperature.

Typical Characteristics

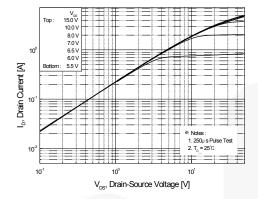


Figure 1. On-Region Characteristics

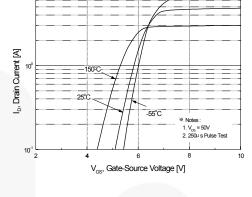


Figure 2. Transfer Characteristics

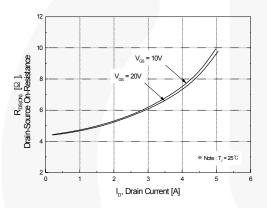


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

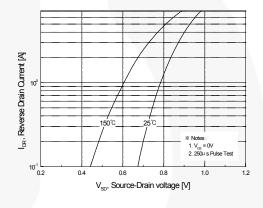


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

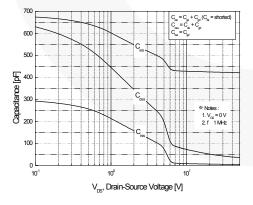


Figure 5. Capacitance Characteristics

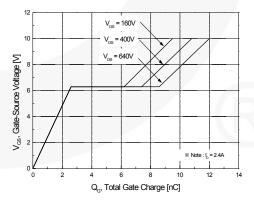


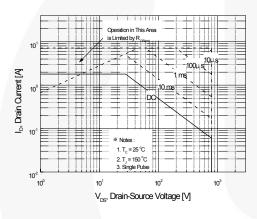
Figure 6. Gate Charge Characteristics

1.2 (Nomalized) 1.1 (Nomalized) 1.0 (Nomalized

Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs Temperature

Figure 8. On-Resistance Variation vs Temperature



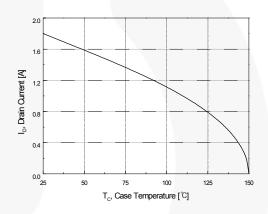


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs Case Temperature

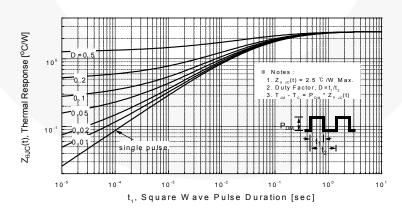


Figure 11. Transient Thermal Response Curve

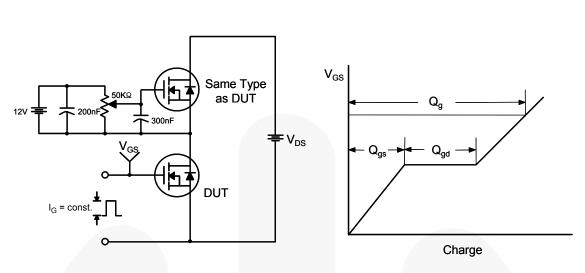


Figure 12. Gate Charge Test Circuit & Waveform

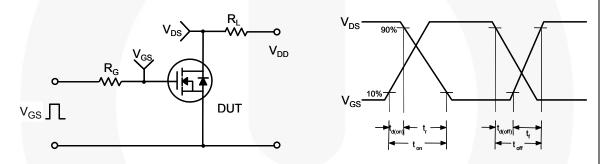


Figure 13. Resistive Switching Test Circuit & Waveforms

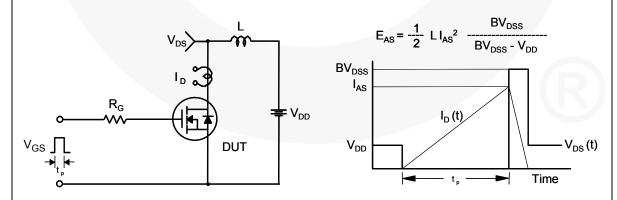
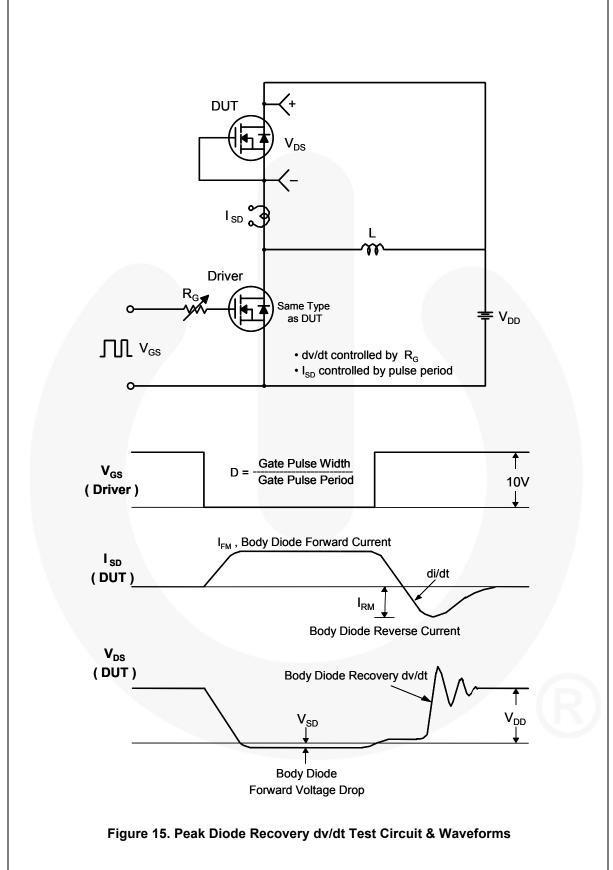


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

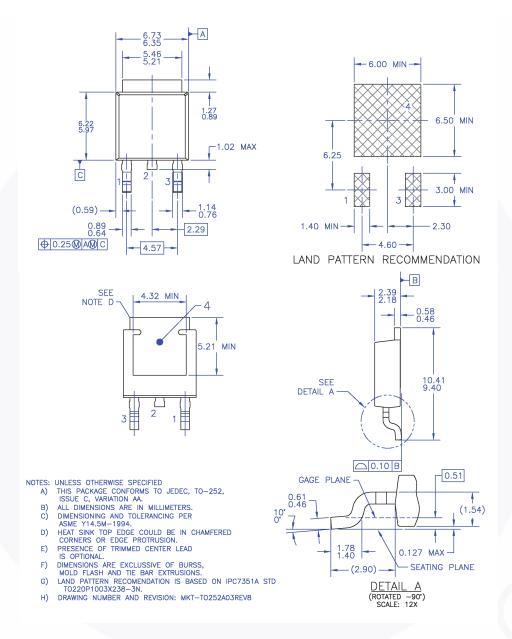


Figure 16. TO252 (D-PAK), Molded, 3-Lead, Option AA&AB

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